

NCE N-Channel Enhancement Mode Power MOSFET

Description

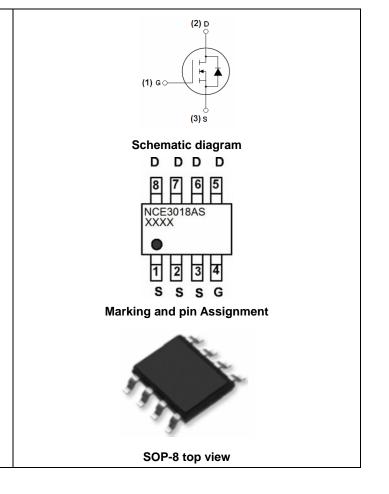
The NCE3018AS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =30V,I_D =18A
 R_{DS(ON)} < 7mΩ @ V_{GS}=10V
 R_{DS(ON)} < 10mΩ @ V_{GS}=4.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3018AS	NCE3018AS	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	18	А
Drain Current-Continuous(T _A =100℃)	I _D (100℃)	12.7	А
Pulsed Drain Current	I _{DM}	72	А
Maximum Power Dissipation	PD	3	W
Single pulse avalanche energy (Note 5)	E _{AS}	204	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	R _{0JA}	42	°C/W	
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Electrical Characteristics (T_A=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	33	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_D=250\mu A$	0.7	1.1	1.4	V
Drain Source On State Desistance	В	V_{GS} =10V, I_{D} =12A	-	5.5	7	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =10A	-	6.5	10	
Forward Transconductance	g fs	V _{DS} =5V,I _D =12A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	2100	-	PF
Output Capacitance	C _{oss}		-	460	-	PF
Reverse Transfer Capacitance	C _{rss}		-	230	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V,I _D =12A V _{GS} =10V,R _{GEN} =2.7Ω	-	20	-	nS
Turn-on Rise Time	tr		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	60	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg		-	41	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =15V,I _D =12A, V _{GS} =10V	-	14	-	nC
Gate-Drain Charge	Q _{gd}	VGS-10V	-	11	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =18A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	18	А

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t ≤ 10 sec.

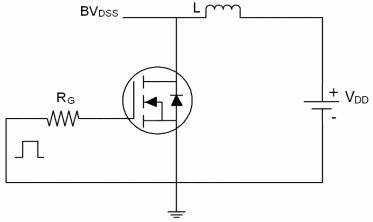
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

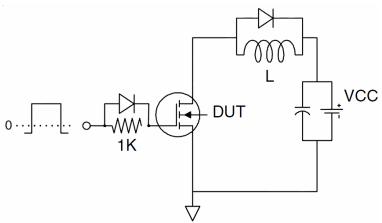
5. E_{AS} condition: Tj=25 $^{\circ}$ C,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25 Ω



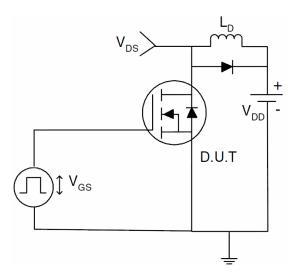
Test Circuit 1) E_{AS} Test Circuits



2) Gate Charge Test Circuit

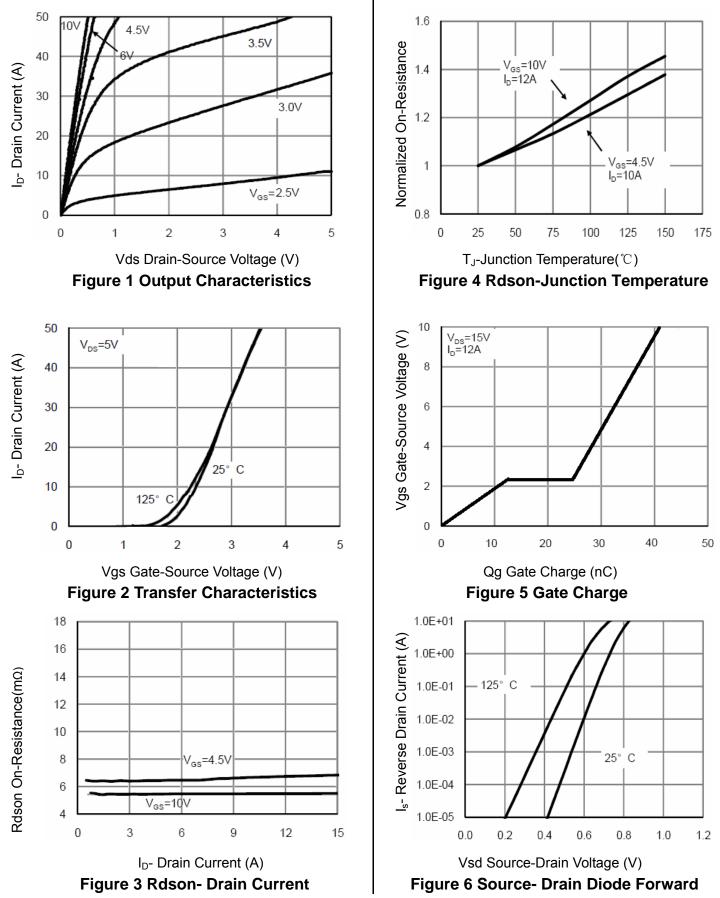


3) Switch Time Test Circuit





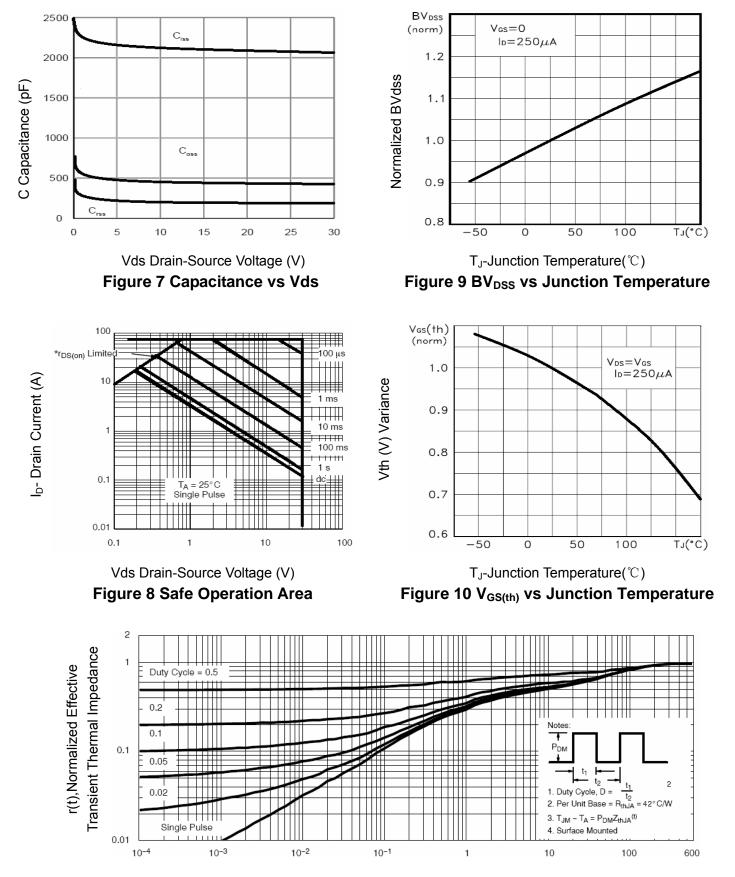
Typical Electrical and Thermal Characteristics (Curves)





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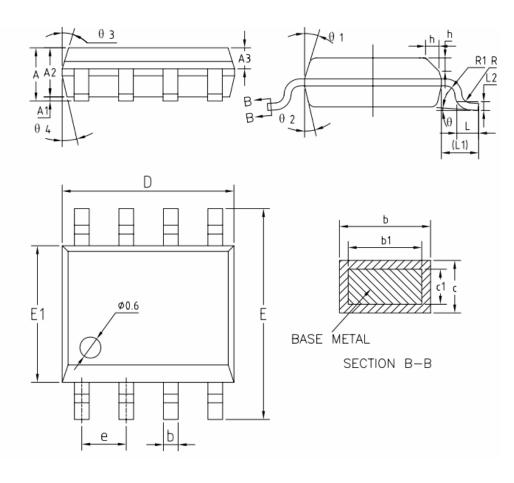
NCE3018AS



Square Wave Pluse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance



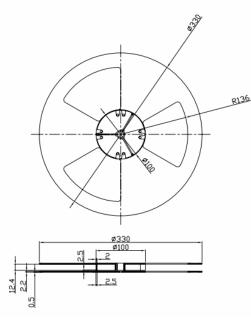
SOP-8 Package Information

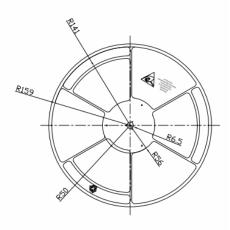


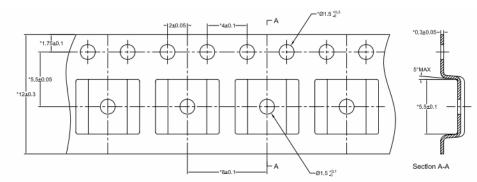
SYMBOL	MIN	NOM	MAX	
A	1.35	1.55	1.75	
A1	0.10	0.15	0.25	
A2	1.25	1.40	1.65	
A3	0.50	0.60	0.70	
b	0.38	-	0.51	
b1	0.37	0.42	0.47	
с	0.18	-	0.25	
c1	0.17	0.20	0.23	
D	4.80	4.90	5.00	
E	5.80	6.00	6.20	
E1	3.80	3.90	4.00	
е	1.17	1.27	1.37	
L	0.45	0.60	0.80	
L1	1.04REF			
L2	0.25BSC			
R	0.07	-	-	
R1	0.07	-	-	
h	0.30	0.40	0.50	
θ	0.	-	8'	
θ1	15'	17 °	19'	
θ2	11	13'	15 °	
θ <u>3</u>	15 '	17'	19 '	
θ4	11'	13 °	15 '	

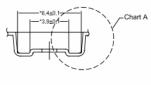
COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

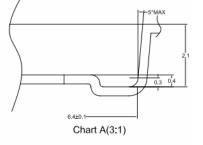




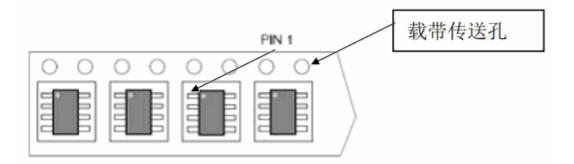








NOTICE: 1.Material: Hard polystyrene 2.AII DIMS IN MM 3.There must nor be foreign adhesion and the state of the surface must be excellent 4. The meander of the tape is assumed with 1mm or less very 100mm between 250mm 5. A permissible difference of the accumulation pitch of the sending hole is assumed to be ±0.3 up to50 pitchs 6. Corner R=0.3max 7. Surface resistance 1×10E5≤Rs≤1×10E12 OHMS/SQ 8.Key size with "*"





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